

Silicon TVS diodes Array

Preliminary Data

 ESD / transient protection of e.g. ADSL, VDSL, ISDN, WAN, LAN, I²C Bus, Microcontroller Inputs, Video and other high-speed data lines in telecom applications:

IEC61000-4-2 (ESD): \pm 15 kV (Air / Contact) IEC61000-4-4 (EFT): 4 kV / 80 A (5/50 ns) IEC61000-4-5 (Lightning): 27 A (8/20 μ s)

- Very low capacitance
- Extremly low reverse current < 5 nA
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



DSL70



Туре	Package	Configuration	Marking
DSL70*	SOT143	2 channel, rail to rail	E4s

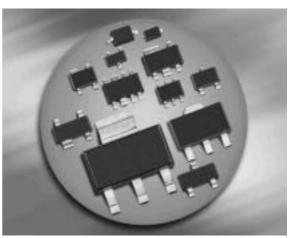
* Preliminary data

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit			
ESD contact discharge per diode ¹⁾	V _{ESD}	15	kV			
Peak pulse current ($t_p = 8 / 20 \ \mu s$) ²⁾	I _{pp}	27	A			
Peak pulse power (<i>t</i> p = 8 / 20 μs)	P _{pk}	245	W			
Operating temperature range	T _{op}	-55125	°C			
Storage temperature	T _{stg}	-65150				

 $^{1}V_{\text{ESD}}$ according to IEC61000-4-2

²I_{pp} according to IEC61000-4-5





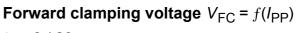
Parameter	Symbol	Values			Unit
		min.	typ.	max.]
Characteristics					
Reverse working voltage	V _{RWM}	-	-	50	V
Reverse current	/ _R	-	-	5	nA
V _R = 50 V					
Forward clamping voltage ¹⁾	V _{FC}				V
$I_{\rm PP}$ = 1 A, $t_{\rm P}$ = 8/20 µs		-	1	1.5	
<i>I</i> _{PP} = 10 A, <i>t</i> _P = 8/20 μs		-	2.5	3	
$I_{\rm PP}$ = 24 A, $t_{\rm P}$ = 8/20 µs		-	5	6	
<i>I</i> _{PP} = 27 A, <i>t</i> _P = 8/20 μs		-	6	9	
Diode capacitance	CT				pF
V_{R} = 0 V, f = 1 MHz, between I/0 and GND		-	2.5	5	
V_{R} = 0 V, f = 1 MHz, between I/0 pins		-	1.25	2.5	

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

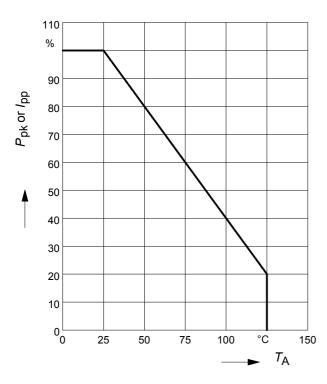
 $^{1}I_{\rm PP}$ according to IEC61000-4-5



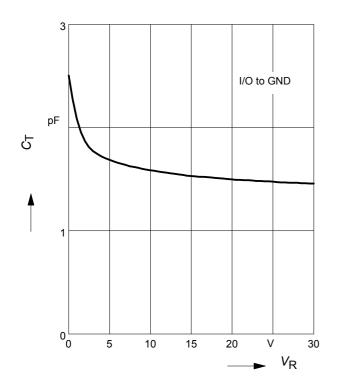
Power derating curve $P_{pk} = f(T_A)$

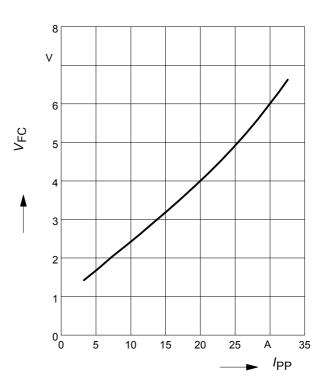


 $t_{\rm p}$ = 8 / 20 µs



Diode capacitance $C_{T} = f(V_{R})$ f = 1MHz

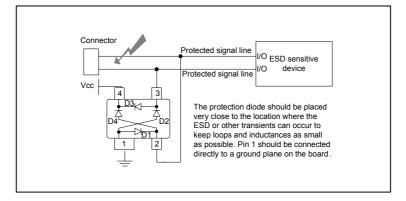




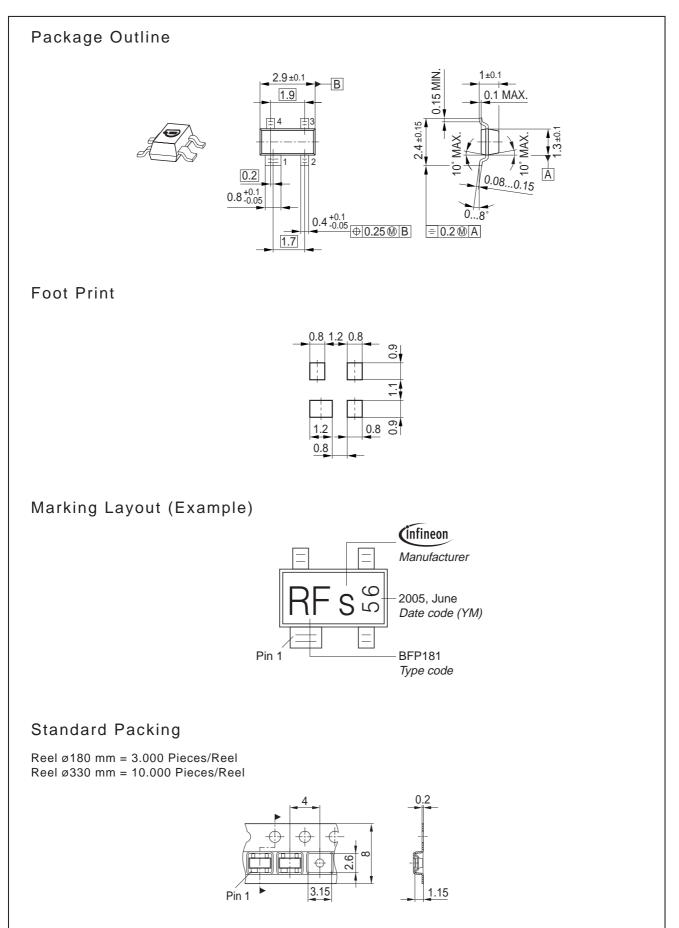


Application example DSL70

dual channel, rail to rail configuration









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